a semiconductor region of the first conduction type formed in the semiconductor substrate surrounded by the buried semiconductor layer and the semiconductor region of the second conduction type,

wherein a concentration of an impurity in the semiconductor region of the first conduction type is equally to a concentration of an impurity in the semiconductor substrate.

REMARKS

By this Amendment, claim 1 is amended. No new matter has been added. Claims 1-7 are pending in this application and are submitted for reconsideration.

Applicants' representative thanks the Examiner for spending time on multiple telephone calls to discuss the present application.

In the Office Action dated February 12, 2002, and in the Advisory Action dated May 29, 2002, claims 1-4 were rejected under 35 U.S.C. § 102(b) as being anticipated by Kenichi et al. (JP 04061269 A). It was submitted in the previous response, and agreed to on a telephone conversation with the Examiner that Kenichi teaches that the concentration of the impurity in the n-well 6 is higher than the concentration of the impurity in the n-type substrate 1. In support, Applicants submit a declaration herewith, which states that Kenichi must teach that the concentration of impurity in n-well 6 is higher than the concentration of the impurity in the n-type substrate 1. In contrast, claim 1 of the present invention recites a concentration of an impurity in a semiconductor region of a first conduction type is equal to a concentration of an impurity in a semiconductor substrate. Thus, Kenichi fails to teach each and every element of claim